

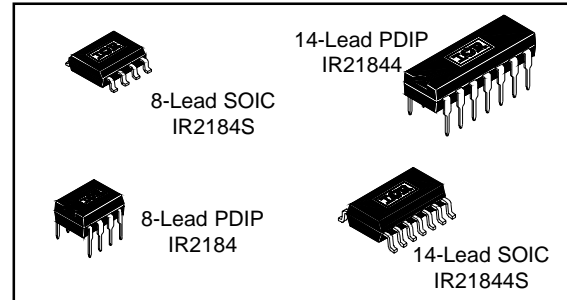
IR2184(4)(S)

HALF-BRIDGE DRIVER

Features

- Floating channel designed for bootstrap operation
Fully operational to +600V
Tolerant to negative transient voltage
dV/dt immune
- Gate drive supply range from 10 to 20V
- Undervoltage lockout for both channels
- 3.3V and 5V input logic compatible
- Matched propagation delay for both channels
- Logic and power ground +/- 5V offset.
- Lower di/dt gate driver for better noise immunity
- Output source/sink current capability 1.4A/1.8A

Packages



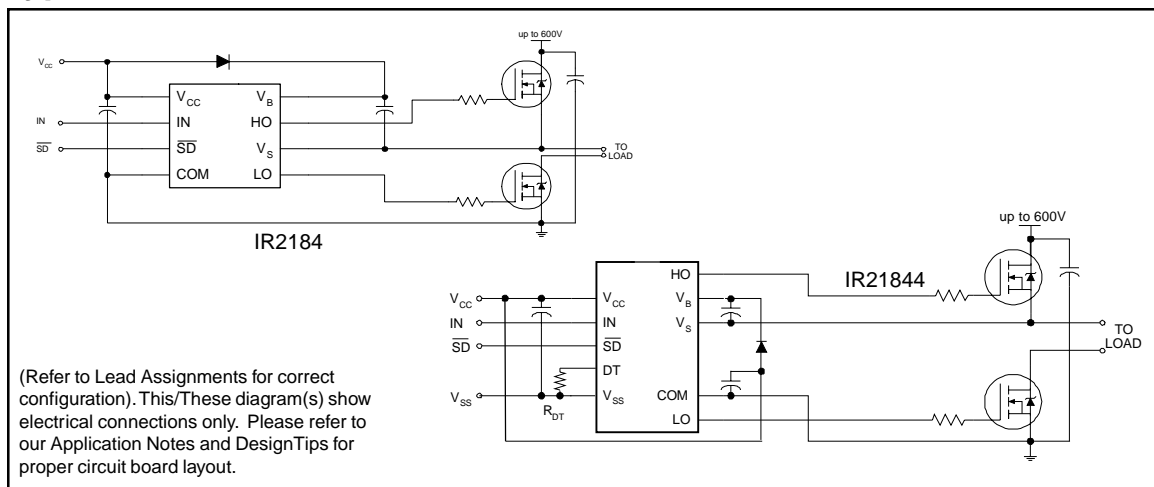
Description

The IR2184(4)(S) are high voltage, high speed power MOSFET and IGBT drivers with dependent high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output, down to 3.3V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates up to 600 volts.

IR2181/IR2183/IR2184 Feature Comparison

Part	Input logic	Cross-conduction prevention logic	Dead-Time	Ground Pins	Ton/Toff
2181	HIN/LIN	no	none	COM	180/220 ns
21814				VSS/COM	
2183	HIN/LIN	yes	Internal 500ns Program 0.4 ~ 5 us	COM	180/220 ns
21834				VSS/COM	
2184	IN/SD	yes	Internal 500ns Program 0.4 ~ 5 us	COM	680/270 ns
21844				VSS/COM	

Typical Connection



IR2184(4) (S)

Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units	
V _B	High side floating absolute voltage	-0.3	625	V	
V _S	High side floating supply offset voltage	V _B - 25	V _B + 0.3		
V _{HO}	High side floating output voltage	V _S - 0.3	V _B + 0.3		
V _{CC}	Low side and logic fixed supply voltage	-0.3	25		
V _{LO}	Low side output voltage	-0.3	V _{CC} + 0.3		
DT	Programmable dead-time pin voltage (IR21844 only)	V _{SS} - 0.3	V _{CC} + 0.3		
V _{IN}	Logic input voltage (IN & \overline{SD})	V _{SS} - 0.3	V _{SS} + 10		
V _{SS}	Logic ground (IR21844 only)	V _{CC} - 25	V _{CC} + 0.3		
dV _S /dt	Allowable offset supply voltage transient	—	50	V/ns	
P _D	Package power dissipation @ T _A ≤ +25°C	(8-lead PDIP)	—	1.0	W
		(8-lead SOIC)	—	0.625	
		(14-lead PDIP)	—	1.6	
		(14-lead SOIC)	—	1.0	
R _{thJA}	Thermal resistance, junction to ambient	(8-lead PDIP)	—	125	°C/W
		(8-lead SOIC)	—	200	
		(14-lead PDIP)	—	75	
		(14-lead SOIC)	—	120	
T _J	Junction temperature	—	150	°C	
T _S	Storage temperature	-50	150		
T _L	Lead temperature (soldering, 10 seconds)	—	300		

Recommended Operating Conditions

The input/output logic timing diagram is shown in figure 1. For proper operation the device should be used within the recommended conditions. The V_S and V_{SS} offset rating are tested with all supplies biased at 15V differential.

Symbol	Definition	Min.	Max.	Units
V _B	High side floating supply absolute voltage	V _S + 10	V _S + 20	V
V _S	High side floating supply offset voltage	Note 1	600	
V _{HO}	High side floating output voltage	V _S	V _B	
V _{CC}	Low side and logic fixed supply voltage	10	20	
V _{LO}	Low side output voltage	0	V _{CC}	
V _{IN}	Logic input voltage (IN & \overline{SD})	V _{SS}	V _{SS} + 5	
DT	Programmable dead-time pin voltage (IR21844 only)	V _{SS}	V _{CC}	
V _{SS}	Logic ground (IR21844 only)	-5	5	
T _A	Ambient temperature	-40	125	°C

Note 1: Logic operational for V_S of -5 to +600V. Logic state held for V_S of -5V to -V_{BS}. (Please refer to the Design Tip DT97-3 for more details).

Note 2: IN and SD are internally clamped with a 5.2V zener diode.

Dynamic Electrical Characteristics

V_{BIAS} (V_{CC}, V_{BS}) = 15V, V_{SS} = COM, C_L = 1000 pF, T_A = 25°C, DT = V_{SS} unless otherwise specified.

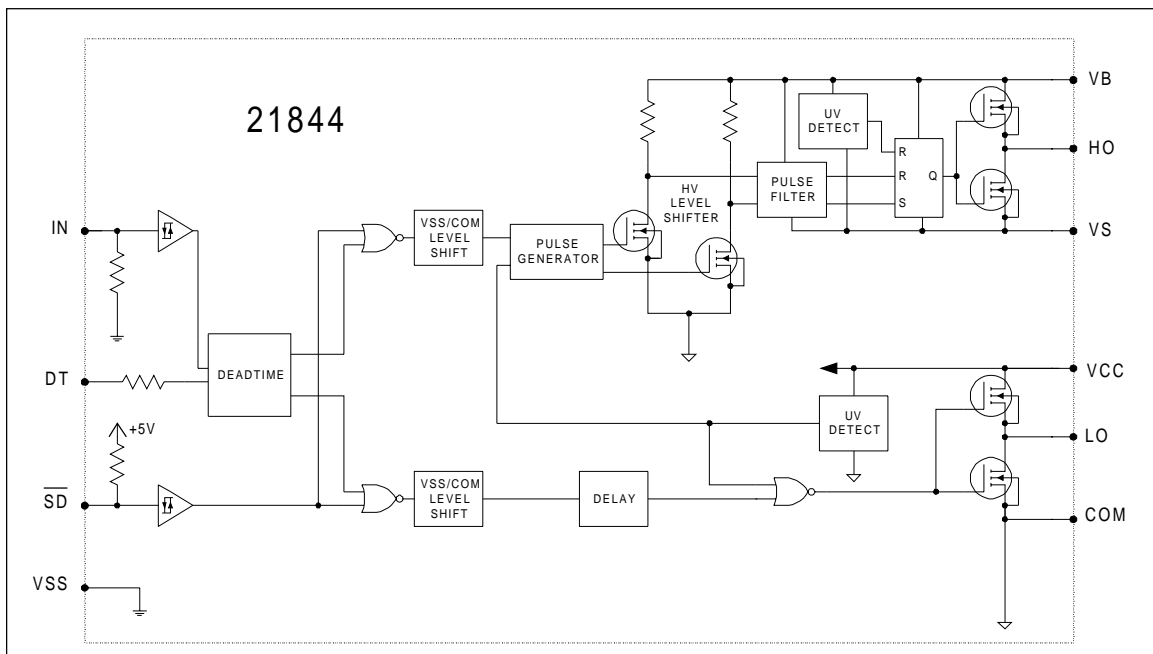
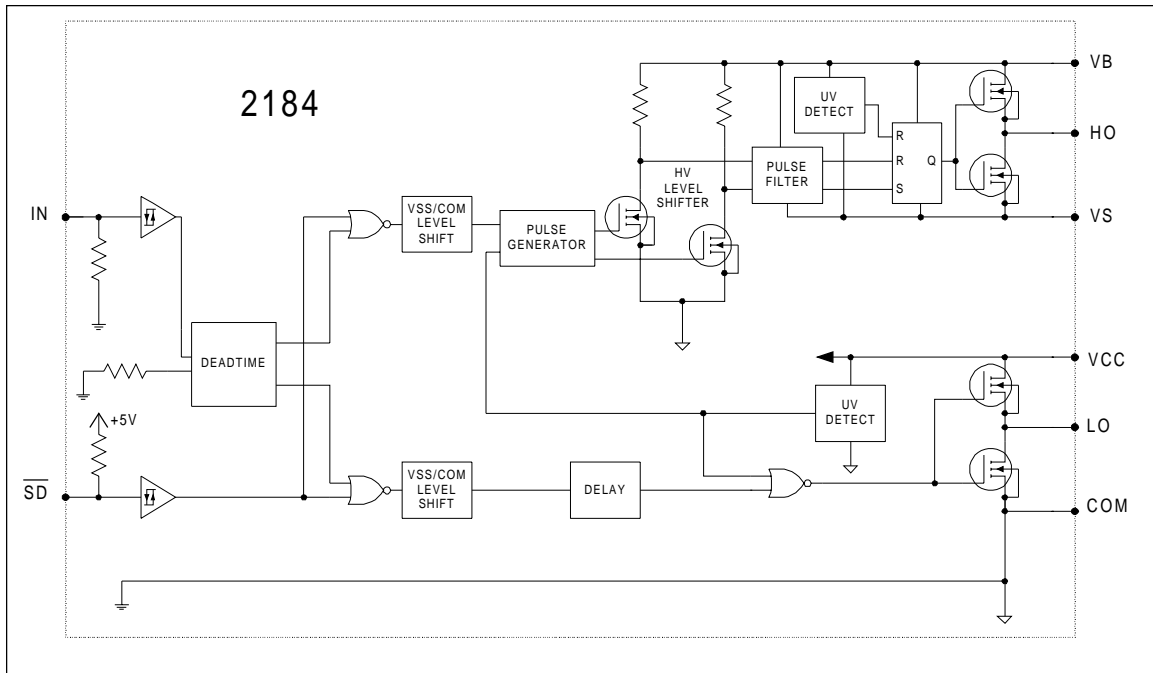
Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
t _{on}	Turn-on propagation delay	—	680	900	nsec	V _S = 0V
t _{off}	Turn-off propagation delay	—	270	400		V _S = 0V or 600V
t _{sd}	Shut-down propagation delay	—	180	270		
M _{Ton}	Delay matching, HS & LS turn-on	—	0	90		
M _{Toff}	Delay matching, HS & LS turn-off	—	0	40		
t _r	Turn-on rise time	—	40	60		V _S = 0V
t _f	Turn-off fall time	—	20	35	V _S = 0V	
DT	Deadtime: LO turn-off to HO turn-on(DT _{LO-HO}) & HO turn-off to LO turn-on (DT _{HO-LO})	280	400	520	μsec	RDT= 0
		4	5	6		RDT = 200k
MDT	Deadtime matching = DT _{LO} - HO - DT _{HO-LO}	—	0	50	nsec	RDT=0
		—	0	600		RDT = 200k

Static Electrical Characteristics

V_{BIAS} (V_{CC}, V_{BS}) = 15V, V_{SS} = COM, DT= V_{SS} and T_A = 25°C unless otherwise specified. The V_{IL}, V_{IH} and I_{IN} parameters are referenced to V_{SS} /COM and are applicable to the respective input leads: IN and SD. The V_O, I_O and Ron parameters are referenced to COM and are applicable to the respective output leads: HO and LO.

Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
V _{IH}	Logic “1” input voltage for HO & logic “0” for LO	2.7	—	—	V	V _{CC} = 10V to 20V
V _{IL}	Logic “0” input voltage for HO & logic “1” for LO	—	—	0.8		V _{CC} = 10V to 20V
V _{SD,TH+}	SD input positive going threshold	2.7	—	—		V _{CC} = 10V to 20V
V _{SD,TH-}	SD input negative going threshold	—	—	0.8		V _{CC} = 10V to 20V
V _{OH}	High level output voltage, V _{BIAS} - V _O	—	—	1.2		I _O = 0A
V _{OL}	Low level output voltage, V _O	—	—	0.1		I _O = 0A
I _{LK}	Offset supply leakage current	—	—	50	μA	V _B = V _S = 600V
I _{QBS}	Quiescent V _{BS} supply current	20	60	150		V _{IN} = 0V or 5V
I _{QCC}	Quiescent V _{CC} supply current	0.4	1.0	1.6	mA	V _{IN} = 0V or 5V
I _{IN+}	Logic “1” input bias current	—	5	20	μA	IN = 5V, SD = 0V
I _{IN-}	Logic “0” input bias current	—	1	2		IN = 0V, SD = 5V
V _{CCUV+} V _{B SUV+}	V _{CC} and V _{BS} supply undervoltage positive going threshold	8.0	8.9	9.8	V	
V _{CCUV-} V _{B SUV-}	V _{CC} and V _{BS} supply undervoltage negative going threshold	7.4	8.2	9.0		
V _{CCUVH} V _{B SUVH}	Hysteresis	0.3	0.7	—		
I _{O+}	Output high short circuit pulsed current	1.4	1.9	—	A	V _O = 0V, PW ≤ 10 μs
I _{O-}	Output low short circuit pulsed current	1.8	2.3	—		V _O = 15V, PW ≤ 10 μs

Functional Block Diagrams



Lead Definitions

Symbol	Description
IN	Logic input for high and low side gate driver outputs (HO and LO), in phase with HO (referenced to COM for IR2184 and VSS for IR21844)
\overline{SD}	Logic input for shutdown (referenced to COM for IR2184 and VSS for IR21844)
DT	Programmable dead-time lead, referenced to VSS. (IR21844 only)
VSS	Logic Ground (21844 only)
V_B	High side floating supply
HO	High side gate drive output
V_S	High side floating supply return
V_{CC}	Low side and logic fixed supply
LO	Low side gate drive output
COM	Low side return

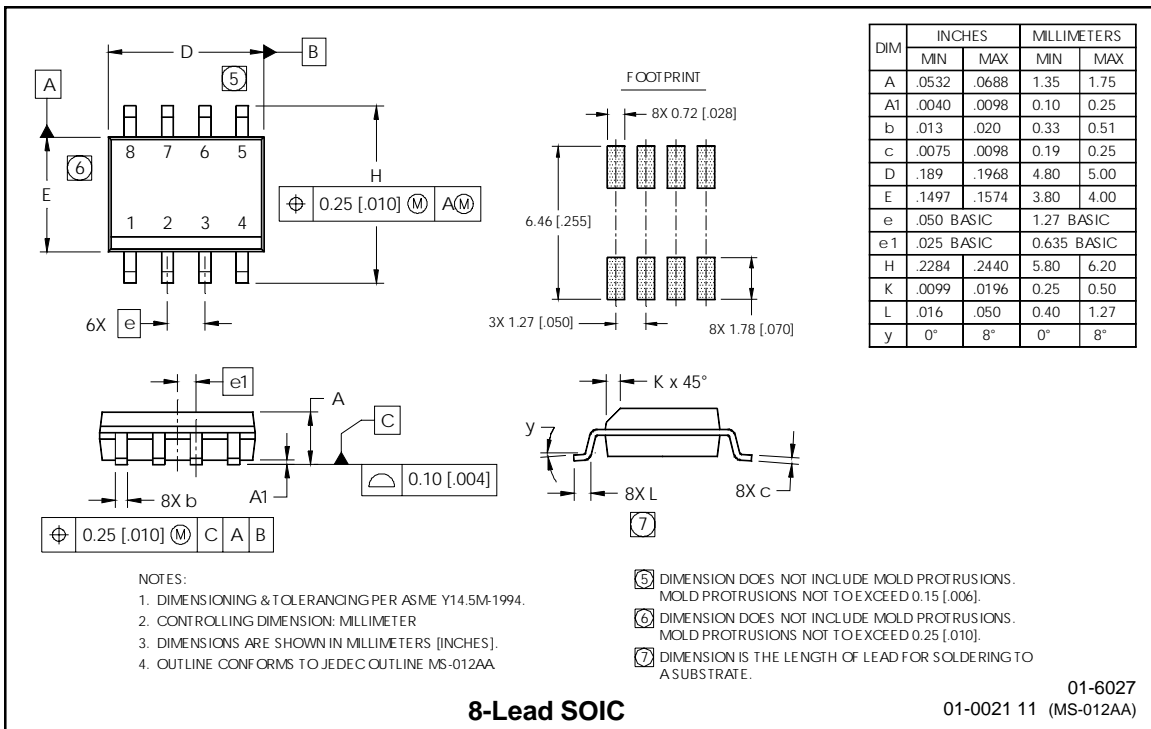
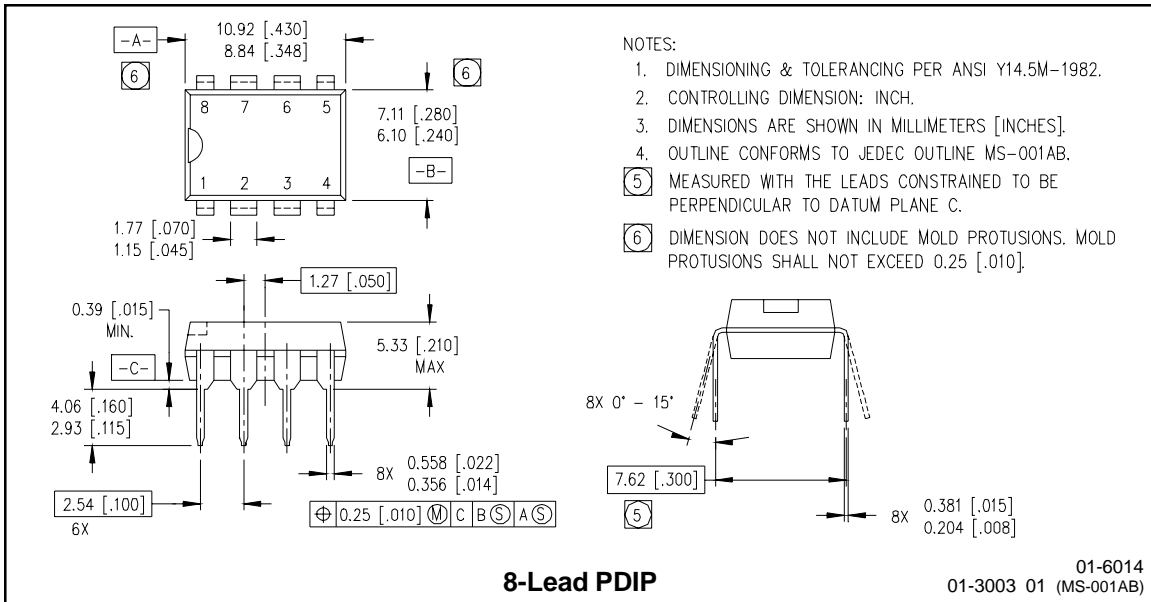
Lead Assignments

<p>8-Lead PDIP</p>	<p>8-Lead SOIC</p>
IR2184	IR2184S

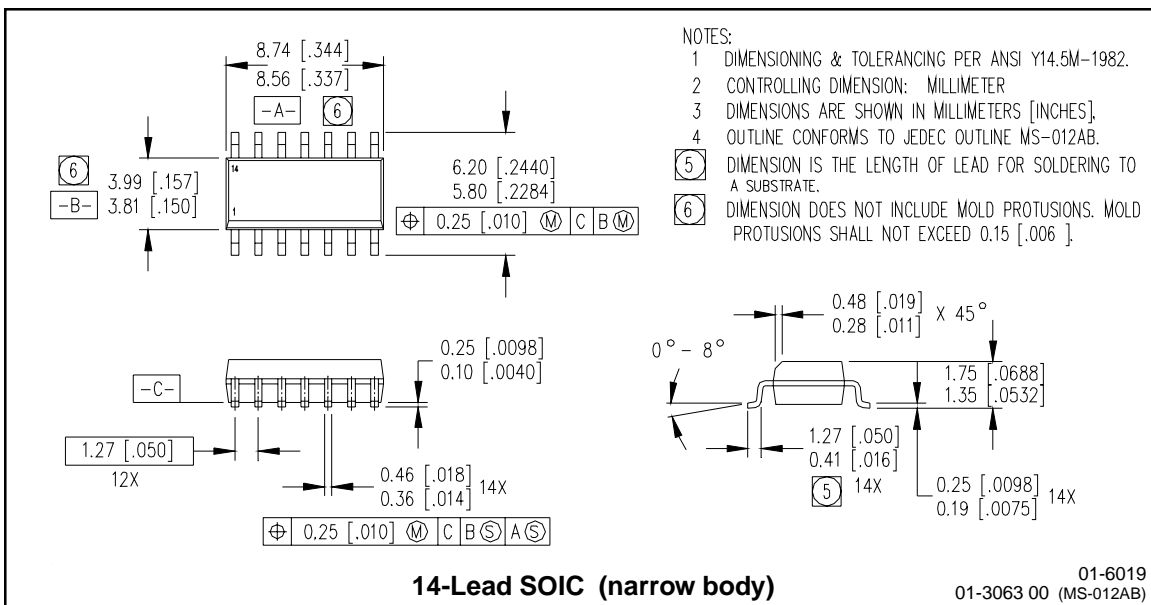
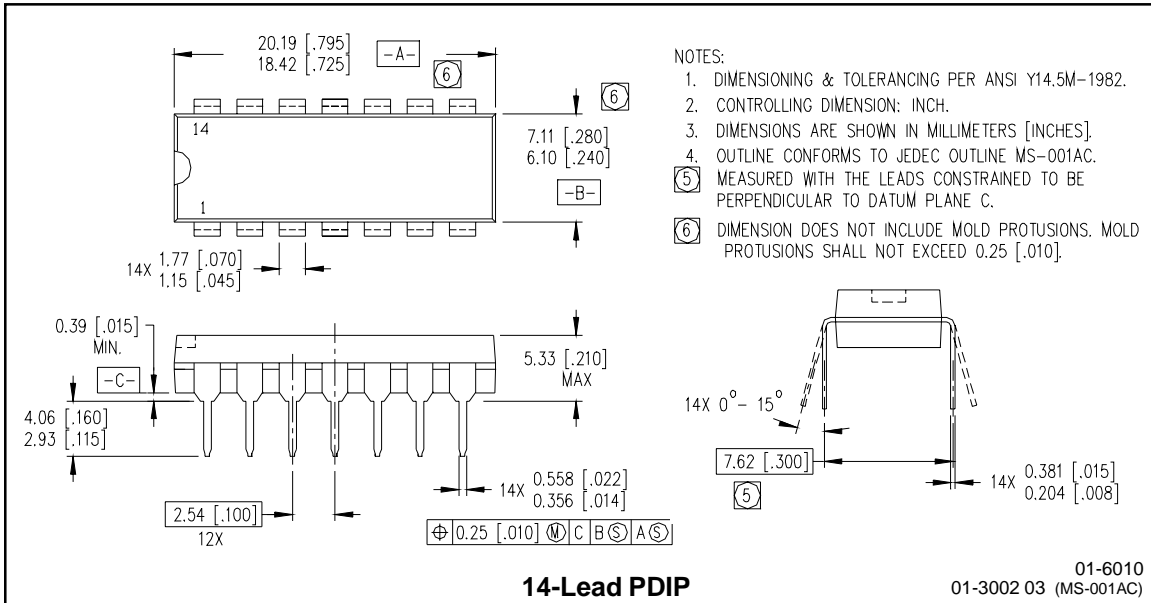
<p>14-Lead PDIP</p>	<p>14-Lead SOIC</p>
IR21844	IR21844S

IR2184(4) (S)

International
IR Rectifier



IR2184(4) (S)



IR2184(4) (S)

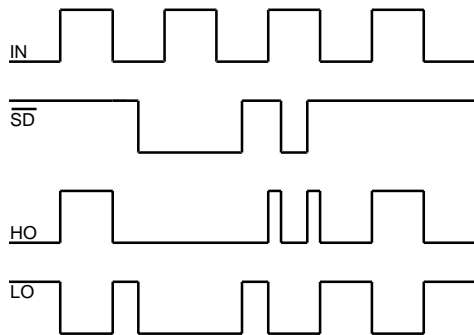


Figure 1. Input/Output Timing Diagram

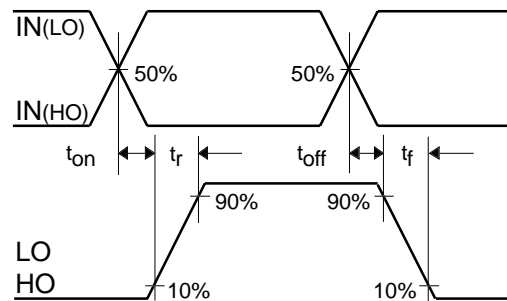


Figure 2. Switching Time Waveform Definitions

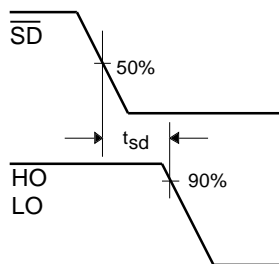


Figure 3. Shutdown Waveform Definitions

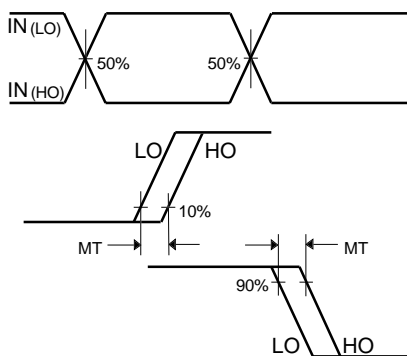


Figure 4. Deadtime Waveform Definitions

Figure 5. Delay Matching Waveform Definitions